

What is claimed is:

1. A method for fabricating a transistor comprising:
  - forming a gate electrode on a semiconductor substrate;
  - forming a first preliminary source/drain region and a pocket junction region through a first ion implantation process using the gate electrode as a mask, the pocket junction region being formed under the first preliminary source/drain region;
  - forming a first oxide layer with uniform thickness on the substrate including the gate electrode;
  - forming a nitride layer with uniform thickness on the first oxide layer;
  - forming a second oxide layer over the nitride layer;
  - forming spacers on sidewalls of the gate electrode;
  - forming a second preliminary source/drain region through a second ion implantation process using the spacers as a mask;
  - removing the nitride layer and the first oxide layer on the surface of the substrate; and
  - diffusing substantially all of the implanted ions in a horizontal direction of the substrate by performing a thermal treatment process for the resulting substrate.
2. The method as defined by claim 1, further comprising performing a thermal treatment process prior to the removal of the nitride layer and the first oxide layer.